



SINGLE P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	11mΩ @ V _{GS} = -10V	-13A
-30V	17mΩ @ V _{GS} = -4.5V	-9.9A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

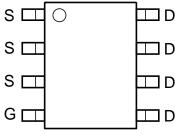
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074g (Approximate)

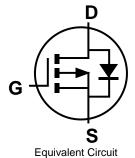
SO-8



Top View



Top View Internal Schematic



Ordering Information (Note 5)

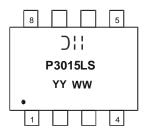
Part Number	Case	Packaging		
DMP3015LSSQ-13	SO-8	2,500/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



);;= Manufacturer's Marking
P3015LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 13 = 2013)
WW = Week (01 - 53)

Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Charac	cteristic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Drain Current (Note 6)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-13 -9.75	Α
Pulsed Drain Current (Note 7)			I _{DM}	-45	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	2.5	W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	50	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

lotes: 6. Device mounted on 2 oz. Copper pads on FR-4 PCB with $R_{\theta JA} = +50^{\circ}$ C/W.

7. Pulse width ≤10µS, Duty Cycle ≤1%.

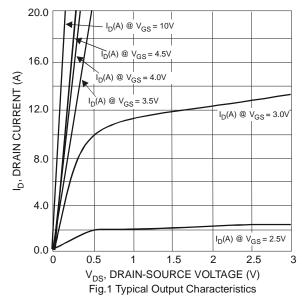


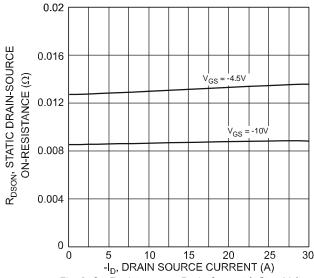
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

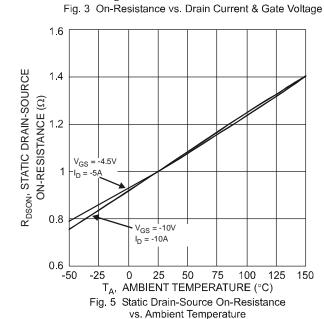
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_		V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-1		-2	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}		9 14	11 17	mΩ	$V_{GS} = -10V, I_D = -13A$ $V_{GS} = -4.5V, I_D = -10A$
Forward Transconductance	9fs	_	15	_	S	$V_{DS} = -15V, I_{D} = -8A$
Diode Forward Voltage (Note 8)	V _{SD}	-0.5	_	-1.1	V	$V_{GS} = 0V, I_{S} = -2.1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	2,748	_	pF	.,
Output Capacitance	Coss	_	357	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	356	_	pF	1 = 1.0iviH2
Gate Resistance	R _G	_	2.0		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$ f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 9)						
Total Gate Charge	Qg	_	30.0 60.4	_		$V_{DS} = -10V$, $V_{GS} = -4.5V$, $I_{D} = -13A$ $V_{DS} = -10V$, $V_{GS} = -10V$, $I_{D} = -13A$
Gate-Source Charge	Q _{gs}	_	7.2	_	nC	$V_{DS} = -10V, V_{GS} = -10V, I_{D} = -13A$
Gate-Drain Charge	Q_{qd}	_	16.4	_		$V_{DS} = -10V, V_{GS} = -10V, I_{D} = -13A$
Turn-On Delay Time	t _{d(on)}	_	11.2	_		
Rise Time	t _r	_	12.4	_	nS	$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{d(off)}	_	104.9	_	110	$I_D = -1A, R_G = 6.0\Omega$
Fall Time	t _f		61.7			

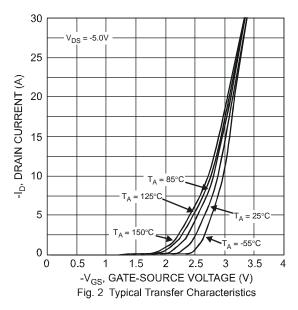
8. Short duration pulse test used to minimize self-heating effect.9. Guaranteed by design. Not subject to product testing. Notes:











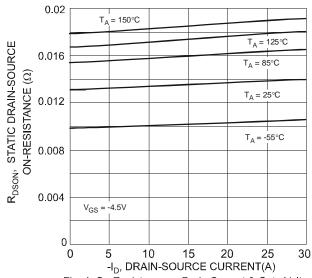
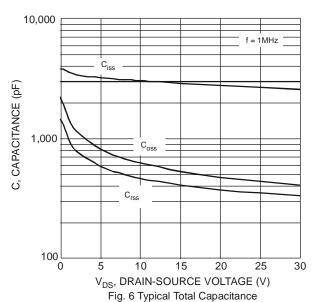


Fig. 4 On-Resistance vs.Drain Current & Gate Voltage





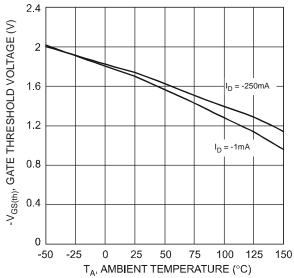


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

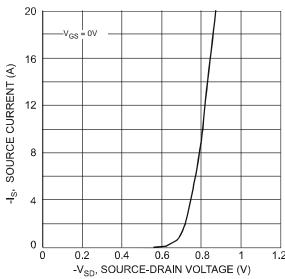
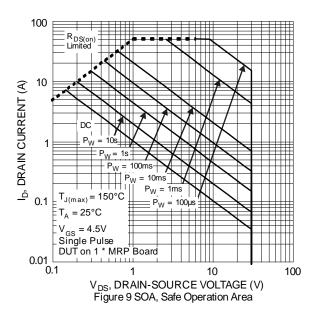
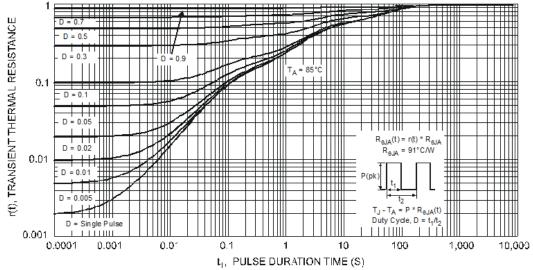


Fig. 8 Forward Drain Current vs. Source-Drain Voltage



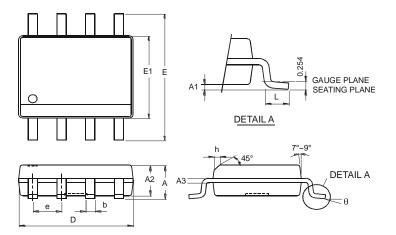




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SO-8

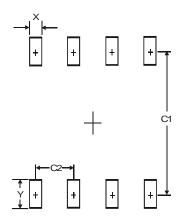


SO-8				
Dim	Min	Max		
Α	_	1.75		
A1	0.08	0.25		
A2	1.30	1.50		
А3	0.20 Typ.			
b	0.3	0.5		
D	4.80	5.30		
Е	5.79	6.20		
E1	3.70	4.10		
е	1.27 Typ.			
h		0.35		
L	0.38	1.27		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SO-8



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27



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